Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	4031	TERA	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:26
S2	21537	TERA or (anti\$reflective with (coating or layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:44
S3	3117	S2 and tun\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:31
S4	14	S3 and carbon and (Si or Ge or Boron) and (anneal\$3 with hydrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:31
S5	1008	S2 and tunable	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:28
S6		S5 and carbon and (anneal\$3 with hydrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:32
S7	9	S5 and (anneal\$3 with hydrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR ·	ON	2005/10/04 15:35
S8	0	S7 and deuterium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:35

S9	14	S1 and deuterium	US-PGPUB;	OR	ON	2005/10/04 15:20
39	14	SI and deuterium	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OK	ON	2005/10/04 15:38
S10	132	S2 and deuterium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 17:13
S11		S2 and (anneal\$3 with deuterium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 10:16
S12	4	(anti\$reflective with (coating or layer)) and (anneal\$3 with deuterium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:54
S13	126	anti\$reflective and deuterium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 15:55
S14	1	S13 and (organo with silicate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 10:42
S15	7	("6147009" "6316167" "6465366" " 6514667" "6537733" "6635583" "67 03169").PN.	US-PGPUB; USPAT	OR .	ON	2005/10/05 14:16
S16	221	S5 and anneal\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/04 16:29
S17	1	("6436799").PN.	USPAT	OR	OFF	2005/10/05 10:19
S18	523	(hydrogen adj annealing) and semiconductor	USPAT	OR	ON	2005/10/05 10:20
S19	16	(hydrogen adj annealing)with (silicon adj oxide)	USPAT	OR	ON	2005/10/05 10:21

S20	0	(deuterium with anneal\$3) and (organo with silicate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 10:42
S21	0	(deuterium with anneal\$3) and (organo adj silicate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 10:43
S22	175	(deuterium with anneal\$3) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 10:43
S23	46	S22 and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 10:43
S24	535	438/781.ccls.	US-PGPUB; USPAT	OR	ON	2005/10/05 14:46
S25	1	S24 and deuterium	US-PGPUB; USPAT	OR	ON	2005/10/05 15:14
S26	31	438/758,761,771,772,776,777, 778-783.ccls. and (deuterium or deuterated)	US-PGPUB; USPAT	OR	ON	2005/10/05 15:17